

Zheng Yang

List of Publications by Year in descending order

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67
papers

4,684
citations

159358

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128067

60
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67
all docs

67
docs citations

67
times ranked

5790
citing authors

#	ARTICLE	IF	CITATIONS
1	Reconfigurable Vanadium Dioxide Nanomembranes and Microtubes with Controllable Phase Transition Temperatures. Nano Letters, 2018, 18, 3017-3023.	4.5	62
2	Synthesis of High-Quality AgSbSe_2 and AgBiSe_2 Nanocrystals with Antimony and Bismuth Silylamide Reagents. Chemistry of Materials, 2017, 29, 4597-4602.	3.2	10
3	Research Update: Spin transfer torques in permalloy on monolayer MoS_2 . APL Materials, 2016, 4, .	2.2	75
4	Regulating Carrier Dynamics in Single Crystal Halide Perovskite via Interface Engineering and Optical Doping. Advanced Electronic Materials, 2016, 2, 1600248.	2.6	11
5	Breakthroughs in Photonics 2014: Phase Change Materials for Photonics. IEEE Photonics Journal, 2015, 7, 1-5.	1.0	21
6	Voltage-Triggered Ultrafast Phase Transition in Vanadium Dioxide Switches. IEEE Electron Device Letters, 2013, 34, 220-222.	2.2	225
7	A perspective of recent progress in ZnO diluted magnetic semiconductors. Applied Physics A: Materials Science and Processing, 2013, 112, 241-254.	1.1	50
8	Thermal tuning of mid-infrared plasmonic antenna arrays using a phase change material. Optics Letters, 2013, 38, 368.	1.7	196
9	Studies on room-temperature electric-field effect in ionic-liquid gated VO_2 three-terminal devices. Journal of Applied Physics, 2012, 111, 014506.	1.1	53
10	Multi-Resistance States Through Electrically Driven Phase Transitions in $\text{VO}_2/\text{HfO}_2/\text{VO}_2$ Heterostructures on Silicon. IEEE Electron Device Letters, 2012, 33, 101-103.	2.2	9
11	Ultra-thin perfect absorber employing a tunable phase change material. Applied Physics Letters, 2012, 101, .	1.5	519
12	Correlated oxide phase transition switch: A paradigm in electron devices. , 2011, , .		0
13	TiSi_2 Nanocrystal Metal Oxide Semiconductor Field Effect Transistor Memory. IEEE Nanotechnology Magazine, 2011, 10, 499-505.	1.1	10
14	Oxide Electronics Utilizing Ultrafast Metal-Insulator Transitions. Annual Review of Materials Research, 2011, 41, 337-367.	4.3	818
15	Work Function of Vanadium Dioxide Thin Films Across the Metal-Insulator Transition and the Role of Surface Nonstoichiometry. ACS Applied Materials & Interfaces, 2011, 3, 3396-3401.	4.0	125
16	Epitaxial Mn-doped ZnO diluted magnetic semiconductor thin films grown by plasma-assisted molecular-beam epitaxy. Journal of Crystal Growth, 2011, 314, 97-103.	0.7	29
17	Direct measurement of compositional complexity-induced electronic inhomogeneity in VO_2 thin films grown on gate dielectrics. Applied Physics Letters, 2011, 98, 192113.	1.5	16
18	Thermal annealing effect on spin coherence in ZnO single crystals. Journal of Applied Physics, 2011, 110, 016101.	1.1	4

#	ARTICLE	IF	CITATIONS
19	Vanadium dioxide (VO_2) is also a ferroelectric: Properties from memory structures. , 2011, , .		2
20	Studies on electric triggering of the metal-insulator transition in VO_2 thin films between 77 K and 300 K. Journal of Applied Physics, 2011, 110, .	1.1	62
21	Geometric confinement effects on the metal-insulator transition temperature and stress relaxation in VO_2 thin films grown on silicon. Journal of Applied Physics, 2011, 109, 063512.	1.1	25
22	Homobuffer thickness effect on the background electron carrier concentration of epitaxial ZnO thin films. Journal of Applied Physics, 2010, 108, 066101.	1.1	5
23	Thermal stability of CdZnO thin films grown by molecular-beam epitaxy. Applied Surface Science, 2010, 256, 4734-4737.	3.1	22
24	Study of rapid thermal annealing effect on CdZnO thin films grown on Si substrate. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2010, 28, C3D13-C3D16.	0.6	3
25	Donor-acceptor-pair photoluminescence in Ga-doped ZnO thin films grown by plasma-assisted molecular beam epitaxy. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2010, 28, C3D6-C3D9.	0.6	6
26	Metal-insulator transition characteristics of VO_2 thin films grown on Ge(100) single crystals. Journal of Applied Physics, 2010, 108, .	1.1	95
27	Na-Doped <i>n</i> -Type ZnO Microwires. Journal of the American Chemical Society, 2010, 132, 2498-2499.	6.6	122
28	Dielectric and carrier transport properties of vanadium dioxide thin films across the phase transition utilizing gated capacitor devices. Physical Review B, 2010, 82, .	1.1	109
29	Ultraviolet light emissions in MgZnO/ZnO double heterojunction diodes by molecular beam epitaxy. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2010, 28, C3D10-C3D12.	0.6	11
30	ZnO:Sb/ZnO:Ga Light Emitting Diode on <i>c</i> -Plane Sapphire by Molecular Beam Epitaxy. Applied Physics Express, 2010, 3, 032101.	1.1	22
31	Microstructure and transport properties of ZnO:Mn diluted magnetic semiconductor thin films. Journal of Applied Physics, 2009, 105, 053708.	1.1	16
32	Temperature-dependent photoluminescence of CdZnO thin films grown by molecular-beam epitaxy. Journal of Crystal Growth, 2009, 312, 68-72.	0.7	9
33	Ga-related photoluminescence lines in Ga-doped ZnO grown by plasma-assisted molecular-beam epitaxy. Applied Physics Letters, 2009, 94, .	1.5	43
34	Blue electroluminescence from ZnO based heterojunction diodes with CdZnO active layers. Applied Physics Letters, 2009, 95, .	1.5	25
35	Cyan electroluminescence from n-ZnO/i-CdZnO/p-Si heterojunction diodes. Materials Research Society Symposia Proceedings, 2009, 1201, 40.	0.1	0
36	Study of the effect of plasma power on ZnO thin films growth using electron cyclotron resonance plasma-assisted molecular-beam epitaxy. Applied Surface Science, 2008, 255, 3375-3380.	3.1	19

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37	Ultraviolet emission from Sb-doped p-type ZnO based heterojunction light-emitting diodes. Applied Physics Letters, 2008, 92, .	1.5	96
38	Electrically pumped ultraviolet ZnO diode lasers on Si. Applied Physics Letters, 2008, 93, .	1.5	267
39	Sb-doped p-ZnO/Ga-doped n-ZnO homojunction ultraviolet light emitting diodes. Applied Physics Letters, 2008, 92, 152103.	1.5	133
40	Electron carrier concentration dependent magnetization and transport properties in ZnO:Co diluted magnetic semiconductor thin films. Journal of Applied Physics, 2008, 104, .	1.1	32
41	Dominant ultraviolet light emissions in packed ZnO columnar homojunction diodes. Applied Physics Letters, 2008, 93, .	1.5	44
42	Electron concentration dependent magnetization and magnetic anisotropy in ZnO:Mn thin films. Applied Physics Letters, 2008, 92, 042111.	1.5	47
43	Influence of electron injection on the temporal response of ZnO homojunction photodiodes. Applied Physics Letters, 2007, 91, .	1.5	7
44	Electron carrier concentration dependent magnetization in ZnO:Co and ZnO:Mn thin films. Materials Research Society Symposia Proceedings, 2007, 1035, 1.	0.1	0
45	Al/Ti contacts to Sb-doped p-type ZnO. Journal of Applied Physics, 2007, 102, 023716.	1.1	31
46	Low-resistivity Au/Ni Ohmic contacts to Sb-doped p-type ZnO. Applied Physics Letters, 2007, 90, 252103.	1.5	27
47	Ultraviolet photoconductive detectors based on Ga-doped ZnO films grown by molecular-beam epitaxy. Solid-State Electronics, 2007, 51, 1014-1017.	0.8	70
48	Homojunction photodiodes based on Sb-doped p-type ZnO for ultraviolet detection. Applied Physics Letters, 2006, 88, 092103.	1.5	98
49	Influence of electron injection on the photoresponse of ZnO homojunction diodes. Applied Physics Letters, 2006, 89, 142114.	1.5	29
50	P-type ZnO by Sb doping for PN-junction photodetectors. , 2006, , .		9
51	ZnO growth on Si with low-temperature ZnO buffer layers by ECR-assisted MBE. Journal of Crystal Growth, 2006, 286, 61-65.	0.7	57
52	ZnO growth on Si with low-temperature CdO and ZnO buffer layers by molecular-beam epitaxy. Journal of Electronic Materials, 2006, 35, 691-694.	1.0	8
53	Bi-induced acceptor states in ZnO by molecular-beam epitaxy. Applied Physics Letters, 2006, 89, 052103.	1.5	33
54	p-type ZnO films with solid-source phosphorus doping by molecular-beam epitaxy. Applied Physics Letters, 2006, 88, 052106.	1.5	114

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55	p-type behavior from Sb-doped ZnO heterojunction photodiodes. Applied Physics Letters, 2006, 88, 112108.	1.5	119
56	Sb surfactant-mediated SiGe graded layers for Ge photodiodes integrated on Si. Journal of Applied Physics, 2006, 99, 024504.	1.1	12
57	Donor and acceptor competitions in phosphorus-doped ZnO. Applied Physics Letters, 2006, 88, 152116.	1.5	94
58	Folded Acoustic Phonon Modes in Ge/Si Quantum Dot Superlattices With Different Periods. Journal of Nanoelectronics and Optoelectronics, 2006, 1, 86-91.	0.1	1
59	Characteristics of a phosphorus-doped <i>p</i> -type ZnO film by MBE. Materials Research Society Symposia Proceedings, 2005, 892, 412.	0.1	2
60	UV photoconductors based on Ga-doped ZnO films. Materials Research Society Symposia Proceedings, 2005, 891, 1.	0.1	1
61	Photoluminescence study of Sb-doped p-type ZnO films by molecular-beam epitaxy. Applied Physics Letters, 2005, 87, 252102.	1.5	197
62	High-mobility Sb-doped p-type ZnO by molecular-beam epitaxy. Applied Physics Letters, 2005, 87, 152101.	1.5	290
63	Optical properties of Ge/Si quantum dot superlattices. Materials Letters, 2004, 58, 3765-3768.	1.3	19
64	Structural characteristics of self-assembled Ge/Si quantum dot superlattices. , 2004, , .		0
65	Strain and Phonon Confinement in Self-Assembled Ge Quantum Dot Superlattices. Chinese Physics Letters, 2003, 20, 2001-2003.	1.3	14
66	Microstructural Models of Alumina Nanotubes and Anodic Porous Alumina Film Formed in Sulphuric Acid. Chinese Physics Letters, 2002, 19, 391-394.	1.3	4
67	A novel approach to evaluate the carrier effective mass in GeSi quantum dot structure. , 0, , .		0